

Tuesday, September 11											
9:00-12:15 Opening & Plenary Sessions (Yasuda Auditorium)											
Lunch											
School of Engineering Bldg.2 North Wing 1F Room 211	School of Engineering Bldg.2 North Wing 1F Room 212	School of Engineering Bldg.2 North Wing 1F Room 213	School of Engineering Bldg.2 North Wing 2F Room 221	School of Engineering Bldg.2 North Wing 2F Room 222	School of Engineering Bldg.2 North Wing 2F Room 223	School of Engineering Bldg.2 North Wing 3F Room 231	School of Engineering Bldg.2 Old Wing 3F Room 233	School of Engineering Bldg.2 North Wing 4F Room 241	School of Engineering Bldg.2 North Wing 4F Room 243	School of Engineering Bldg.2 North Wing 4F Room 244	School of Engineering Bldg.2 Old Wing 4F Room 246
14:00-15:15	14:00-15:15	14:00-15:15	14:00-15:15		14:00-15:15	14:00-15:15	14:00-15:15	14:00-15:15	14:00-15:15	14:00-15:15	14:00-15:15
A-1:Spin Transport	B-1:ReRAM	C-1:Nanowire and Nanostructure-Based FET	D-1:GaN Device Technologies I		F-1:High-Capacity-Anode Materials (Li, Si)	G-1:Interconnect-I	H-1:Germanium for Photonics Applications	J-1:Innovative Device Based Circuits I	K-1:Organic Light Emitting and Sensing Devices	M-1:Quantum Nano Photonics	N-1:Novel Thin Film Materials and Devices
Coffee Break											
15:30-17:15	15:30-16:30	15:30-16:30	15:30-17:15		15:30-16:45		15:30-16:45	15:30-17:15 Area7 & Special	15:30-16:45 Area3 & 7	15:30-17:15	15:30-16:45
A-2:Spintronics for AI and LSI Applications	B-2:Selector for Memory	C-2:Transistor Physics and Reliability	D-2:SiC MOS Interface		F-2:Battery / Fuel Cell		H-2:Si Photonic Integrated Circuits	J-2:Ion/Photon Coupled Systems	K-2:Organic Printing and Patterning Technologies	M-2:Optical Properties of 2D Materials	N-2:Crystal Growth of Group IV and Related Materials I
Departure 19:20 / Arrival 21:20 Banquet Cruise Departure											
Wednesday, September 12											
School of Engineering Bldg.2 North Wing 1F Room 211	School of Engineering Bldg.2 North Wing 1F Room 212	School of Engineering Bldg.2 North Wing 1F Room 213	School of Engineering Bldg.2 North Wing 2F Room 221	School of Engineering Bldg.2 North Wing 2F Room 222	School of Engineering Bldg.2 North Wing 2F Room 223	School of Engineering Bldg.2 North Wing 3F Room 231	School of Engineering Bldg.2 Old Wing 3F Room 233	School of Engineering Bldg.2 North Wing 4F Room 241	School of Engineering Bldg.2 North Wing 4F Room 243	School of Engineering Bldg.2 North Wing 4F Room 244	School of Engineering Bldg.2 Old Wing 4F Room 246
9:00-10:30	9:00-10:30	9:00-10:30	9:00-10:30	9:00-10:30	9:15-10:30	9:00-10:15	9:00-10:30	9:00-10:30 Area7 & Special	9:00-10:15	9:00-10:30	9:00-10:30
A-3:Quantum Phenomena	B-3:In-Memory Computing I	C-3:Characterization and Process Technology	D-3:Ultrawide-Bandgap Semiconductor Devices I	E-3:Characterizations of Gate Dielectrics	F-3:Perovskite	G-3:3D Intergration	H-3:Heterogeneous Photonic Integrated Circuits on Si	J-3:Innovative Device Based Circuits II	K-3:Bio and Micro Systems	M-3:2D Materials & Devices I	N-3:Oxide Materials and Advanced Devices
Coffee Break											
10:45-12:00	10:45-12:00	10:45-12:00	10:45-12:00	10:45-12:00	10:45-12:00	10:45-11:45	10:45-12:00	10:45-12:00 Area10 & Special	10:45-11:45	10:45-12:00	
A-4:Electrical Control of Magnetism	B-4:In-Memory Computing II	C-4:Ferroelectric and Tunnel FET I	D-4:Ultrawide-Bandgap Semiconductor Devices II	E-4:Advanced Materials Synthesis and Simulation	F-4:Perovskite	G-4:Advanced Bonding	H-4:Integration Technology for Photonic Applications	J-4:Thin Film Oxide Materials Based Devices and Systems	K-4:Organic Memory, Actuator and Sensing Devices	M-4:Nanowire Growth & Characterization	
Lunch											
Luncheon Seminar: Tektronix											
13:30-15:00	13:30-15:00	13:30-15:00 Area1 & 2	13:30-15:00	13:30-15:00	13:30-15:00		13:45-15:00	13:30-15:00 Area7 & Special	13:30-14:45	13:30-15:00	13:30-14:30
A-5:Novel Functional Devices	B-5:Gate Stack and Interface Engineering	C-5:Ferroelectric Hafnium Oxide: Breakthrough in Transistor and Memory I	D-5:High Frequency Devices/Narrow Gap Devices	E-5:Nanostructures: Synthesis and Properties	F-5:Si and Compounds		H-5:Photonic Devices and Platforms for Novel Applications	J-5:Biomedical Devices and Systems	K-5:Organic Transistors	M-5:Physics & Application of Graphene Devices	N-5:Poly-Si TFT Technologies and Circuit Applications
Coffee Break											
15:15-16:30	15:15-16:30	15:15-16:30 Area1 & 2	15:15-16:30	15:15-16:30	15:15-16:30	15:15-16:15	15:15-16:15	15:15-17:00	15:15-16:30	15:15-16:30	15:15-16:30
A-6:New Materials and Physics in Spintronics	B-6:Process Technology	C-6:Ferroelectric Hafnium Oxide: Breakthrough in Transistor and Memory II	D-6:Silicon Devices and Processes	E-6:Group IV Materials	F-6:Quantum Dot	G-6:Interconnect-II	H-6:Hybrid Devices and Materials	J-6:Advanced Image Sensors	K-6:Biodevices and Materials	M-6:Nano-Structure Devices	N-6:New Functional Materials and Devices
16:30-17:15	16:30-17:15	16:30-17:15	16:30-17:15		16:30-17:15			17:00-17:15	16:30-17:15	16:30-17:15	16:30-17:15
Short Presentation Area9	Short Presentation Area2	Short Presentation Area1	Short Presentation Area4		Short Presentation Area6			Short Presentation Special Area	Short Presentation Area7	Short Presentation Area8	Short Presentation Area10
	Short Presentation Area3		Short Presentation Area11								Short Presentation Area5
17:30-19:30 Rump Sessions (Faculty of Engineering Bldg.2 Room 213)											
Thursday, September 13											
School of Engineering Bldg.2 North Wing 1F Room 211	School of Engineering Bldg.2 North Wing 1F Room 212	School of Engineering Bldg.2 North Wing 1F Room 213	School of Engineering Bldg.2 North Wing 2F Room 221	School of Engineering Bldg.2 North Wing 2F Room 222	School of Engineering Bldg.2 North Wing 2F Room 223	School of Engineering Bldg.2 North Wing 3F Room 231	School of Engineering Bldg.2 Old Wing 3F Room 233	School of Engineering Bldg.2 North Wing 4F Room 241	School of Engineering Bldg.2 North Wing 4F Room 243	School of Engineering Bldg.2 North Wing 4F Room 244	School of Engineering Bldg.2 Old Wing 4F Room 246
9:00-10:45	9:00-10:45	9:00-10:45	9:00-10:45	9:00-10:45	9:45-10:45	9:00-10:45		9:00-10:45 Area5 & Special	9:00-11:00	9:00-10:30	9:00-10:15
A-7:Quantum Computational Devices	B-7:Flash and 1T-DRAM	C-7:Ferroelectric and Tunnel FET II	D-7:GaN Device Technologies II	E-7:Advanced Growth of Widegap Semiconductors	F-7:Photocatalyst/Solar Cells	G-7:MEMS Application		J-7:LiDAR and Imaging Applications	K-7:Chemical and Gas Sensors	M-7:2D Materials & Devices II	N-7:Advanced IGZO Processes and Devices
Coffee Break											
11:00-13:30 Poster Session (Ito International Resrch Center, Ito Hall)											
Lunch											
14:00-16:00		14:00-15:45	14:00-15:45		14:00-15:45 Area6 & 11		14:00-15:30	14:00-16:00 Area1 & Special	14:00-15:30		14:00-15:15
A-8:Spin-Orbit Interaction		C-8:Group III-V and Ge Technology	D-8:SiC Devices and Processes		F-8:Thermoelectric Materials		H-8:Light Emitting Devices and Photodiodes	J-8:Innovative Device Based Circuits III	K-8:Molecular Materials and Devices		N-8:Crystal Growth of Group IV and Related Materials II

Area Scope		Area 1: Advanced CMOS: Material Fundamentals, Process Science and Device Physics
		Area 2: Advanced / Emerging Memories and New Applications
		Area 3: Interconnect / 3D Integrations / MEMS
		Area 4: Power / High-speed Devices, and Materials
		Area 5: Advanced Photonics: Devices, Integration and Related Technology
		Area 6: Photovoltaic / Energy Harvesting / Battery-related Technology
		Area 7: Organic / Molecular / Bio-electronics
		Area 8: Low Dimensional Devices and Materials

Area Scope		Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
		Area 10: Thin Film Electronics: Oxide, Non-single Crystalline and Novel Process
		Area 11: Advanced Materials Synthesis and Advanced Characterization
		Special Area: Advanced Circuits/Systems Interacting with Innovative Devices & Materials